Supplemental Information

The Initial Stages of ZnO Atomic Layer Deposition on Atomically Flat In$_{0.53}$Ga$_{0.47}$As Substrates

By E.V. Skopin et al.

Figure S1. 3D rendering of the same AFM images shown in Fig. 5 of the article, i.e. post-growth AFM images of ZnO films grown on In$_{0.53}$Ga$_{0.47}$As for different number of cycles: 0 (a), 5 (b), 10 (c), 15 (d), 20 (e), 25 (f), 30 (g), 40 (h) and 50 (i).
Figure S2. Statistical distribution of the terrace heights present on the In$_{0.53}$Ga$_{0.47}$As substrate surface after the 4M HCl etch step. The height value is in $a$ units, where $a$ is the bulk In$_{0.53}$Ga$_{0.47}$As lattice parameter. A series of parallel lines were chosen with a constant distance between the lines for the analysis. The peaks of the statistical distribution have been approximated by a Gaussian function.
Figure S3: Zn Kα X-ray fluorescence intensity (T substrate = 120°C) vs. cycle number for three different water flow (deionized water). The increasing of water flow is obtained by opening the injector aperture (2, 6, 9 are the numbers of turns of the manual needle valve). Clearly, increasing the water flow shortens the delay in ZnO nucleation.